Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of cleaning an annealed silicon wafer, consisting essentially of the steps of:

    oxidizing ~~an annealed silicon wafer~~ <u>a silicon wafer annealed under an environment of hydrogen gas</u> with ozonized water;

    cleaning the oxidized silicon wafer with hydrofluoric acid; and,

    as a final cleaning step, oxidizing the silicon wafer with ozonized water, thus obtaining a silicon wafer in which micro roughness thereof under a spatial frequency of $20/\mu m$ is 0.3 to 1.5 nm^3 in terms of power spectrum density.

2. (Previously Presented) The method according to claim 1, wherein the final step of oxidizing with ozonized water takes place just after the oxidation step and the hydrofluoric acid cleaning step.

3. (Previously Presented) The method according to claim 1, wherein the concentration of the ozonized water is 10 to 60 ppm.

4. (Previously Presented) The method according to claim 1, wherein the concentration of the hydrofluoric acid is 0.5 to 2%.

5. (Previously Presented) The method according to claim 1, wherein an oxide film is present on the surface of the silicon wafer at the completion of the cleaning method.

6-10. (Canceled)